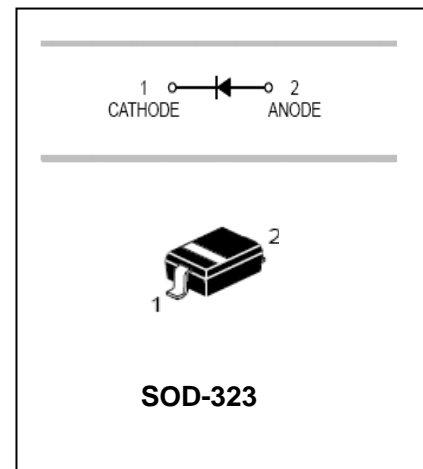


Silicon Epitaxial Planar Diode

1SS380

FEATURES

- Small surface mounting type
- High speed
- Suitable for high packing density



APPLICATIONS

- High speed switching

ORDERING INFORMATION

Type No.	Marking	Package Code
1SS380	6D	SOD-323

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC Reverse Voltage	V_R	35	V
Peak forward Current	I_{FSM}	225	mA
Average Rectified Output Current	I_O	100	mA
Surge current(1s)	I_{surge}	400	mA
Power Dissipation	P_D	200	mW
Junction temperature	T_j	125	°C
Storage temperature	T_{STG}	-55 to+125	°C

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F			1.2	V	$I_F=100mA$
Reverse current	I_R			10	nA	$V_R=20V$
Capacitance between terminals	C_T			5	pF	$V_R=0.5V, f=1MHz$

Silicon Epitaxial Planar Diode

1SS380

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

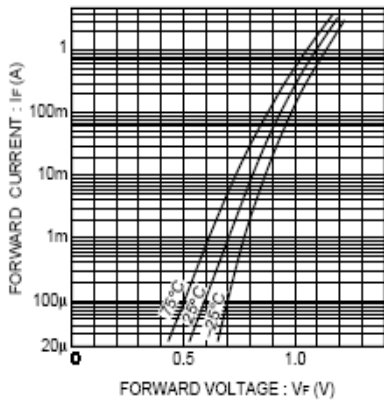


Fig. 1 Forward characteristics

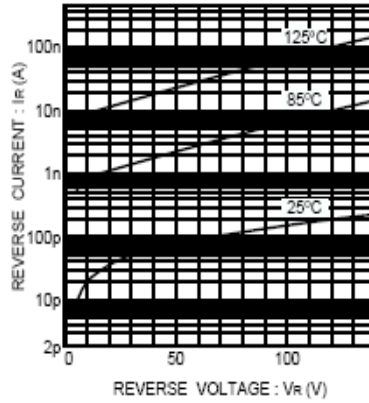


Fig. 2 Reverse characteristics

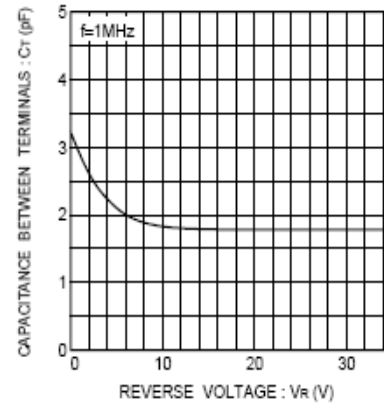


Fig. 3 Capacitance between terminals characteristics

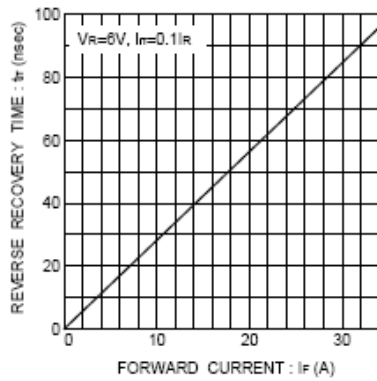


Fig. 4 Reverse recovery time characteristics

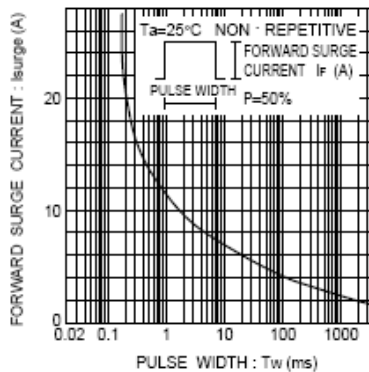


Fig. 5 Surge current characteristics

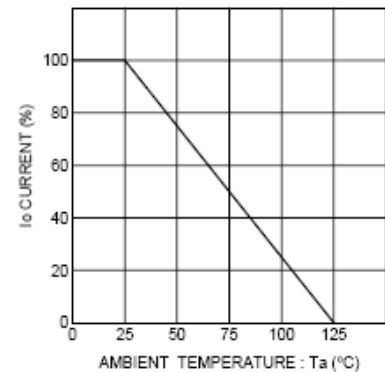


Fig. 6 Derating curve (mounting on glass epoxy PCBs)

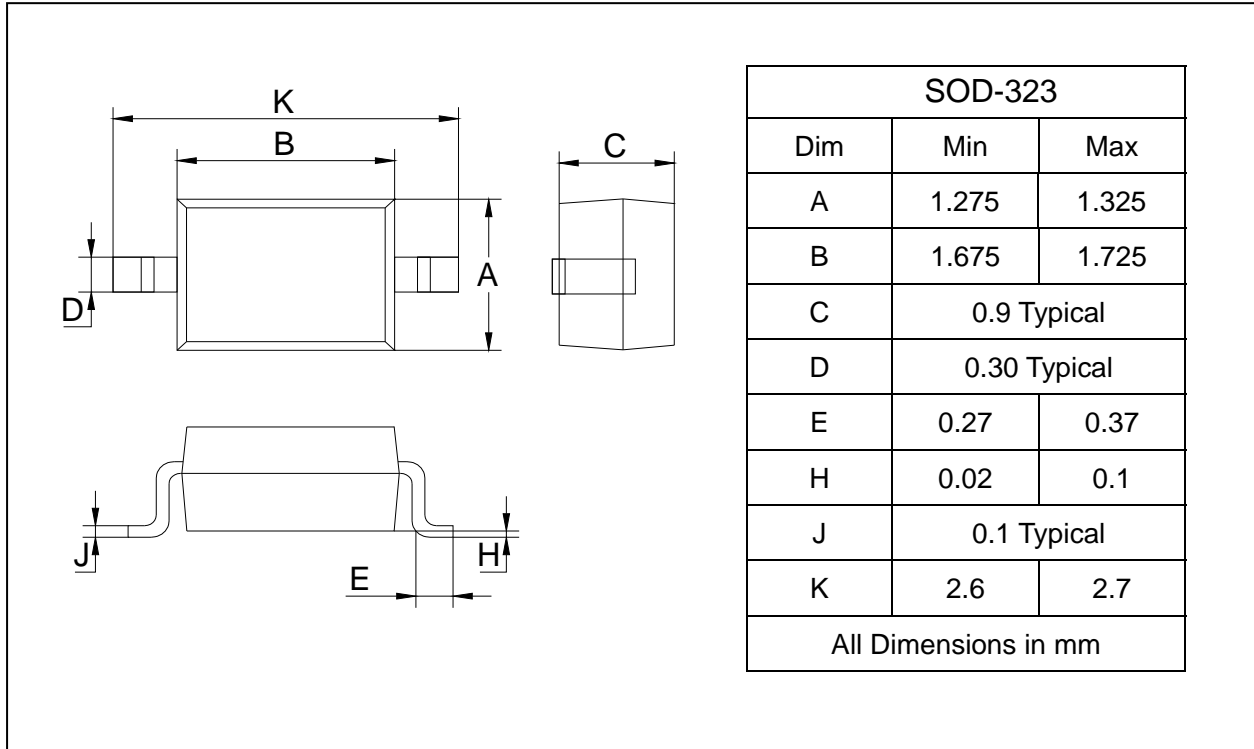
Silicon Epitaxial Planar Diode

1SS380

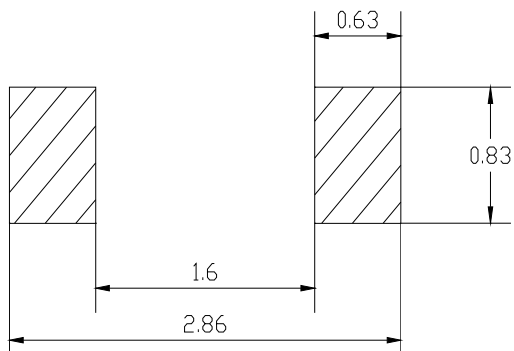
PACKAGE OUTLINE

Plastic surface mounted package

SOD-323



SOLDERING FOOTPRINT



Unit : mm

PACKAGE INFORMATION

Device	Package	Shipping
1SS380	SOD-323	3000/Tape&Reel